

HG RF POWER TRANSISTOR MRF323

ROHS Compliance, Silicon NPN POWER TRANSISTOR

- \dots designed primarily for wideband large–signal driver and predriver amplifier stages in the 200–500 MHz frequency range.
- ω Guaranteed Performance at 400 MHz, 28 V

Output Power = 20 Watts

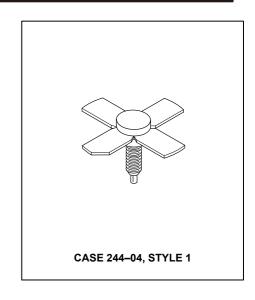
Power Gain = 10 dB Min

Efficiency = 50% Min

- $\,\omega\,$ 100% Tested for Load Mismatch at all Phase Angles with 30:1 VSWR
- ω Gold Metallization System for High Reliability
- ω Computer-Controlled Wirebonding Gives Consistent Input Impedance

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	33	Vdc
Collector–Base Voltage	VCBO	60	Vdc
Emitter–Base Voltage	VEBO	4.0	Vdc
Collector Current — Continuous — Peak	IC	2.2 3.0	Adc
Total Device Dissipation @ T _C = 255C (1) Derate above 255C	PD	55 310	Watts mW/5C
Storage Temperature Range	T _{stg}	-65 to +150	5C



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.2	5C/W

ELECTRICAL CHARACTERISTICS ($T_C = 255C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, I _B = 0)	V _(BR) CEO	33	_	_	Vdc
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, V _{BE} = 0)	V _(BR) CES	60	_	_	Vdc
Collector–Base Breakdown Voltage (I _C = 20 mAdc, I _E = 0)	V _(BR) CBO	60	_	_	Vdc
Emitter–Base Breakdown Voltage (IE = 2.0 mAdc, IC = 0)	V _{(BR)EBO}	4.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	ІСВО	_	_	2.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc)	h _{FE}	20	_	80	_
DYNAMIC CHARACTERISTICS	•				
Output Capacitance (V _{CB} = 28 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	20	24	pF
FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V _{CC} = 28 Vdc, P _{out} = 20 W, f = 400 MHz)	GPE	10	11	_	dB .
Collector Efficiency (V _{CC} = 28 Vdc, P _{out} = 20 W, f = 400 MHz)	η	50	60	_	%
Load Mismatch (V _{CC} = 28 Vdc, P _{out} = 20 W, f = 400 MHz, VSWR = 30:1 all phase angles)	ψ	No Degradation in Output Power			

Note: Above parameters, ratings, limits and conditions are subject to change.

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